

2N1040 Transistors

Ge PNP Power BJT

Military/High-Rel N

$V_{(BR)CEO}$ (V) 80°

$V_{(BR)CBO}$ (V) 80

I_C Max. (A) 3.0

Absolute Max. Power Diss. (W) 20

Maximum Operating Temp (θ_C) 100#

I_{CBO} Max. (A) 125u

@ V_{CBO} (V) (Test Condition) 40

$V_{(CE)sat}$ Max. (V) .25

@ I_C (A) (Test Condition) 1.0

@ I_B (A) (Test Condition) 100m

h_{FE} Min. Current gain. 33

h_{FE} Max. Current gain. 200

@ I_C (A) (Test Condition) 50m

@ V_{CE} (V) (Test Condition) .50

f_T Min. (Hz) Transition Freq

@ I_C (A) (Test Condition)

@ V_{CE} (V) (Test Condition)

t_r Max. (s) Rise time

t_f Max. (s) Fall time.

Package Style Can

Datasheet.Wiki